Nguyen Tien Son

List of Publications by Citations

226 papers	6,162 citations	41 h-index	69 g-index
238 ext. papers	7,050 ext. citations	3.4 avg, IF	5.42 L-index

#	Paper	IF	Citations
226	Coherent control of single spins in silicon carbide at room temperature. *Nature Materials*, **2015**, 14, 164-8	27	347
225	Isolated electron spins in silicon carbide with millisecond coherence times. *Nature Materials*, **2015**, 14, 160-3	27	278
224	Deep level defects in electron-irradiated 4H SiC epitaxial layers. *Journal of Applied Physics*, **1997**, 81, 6155-6159	2.5	241
223	Silicon vacancy related defect in 4H and 6H SiC. *Physical Review B*, **2000**, 61, 2613-2620	3.3	202
222	Negative-U system of carbon vacancy in 4H-SiC. *Physical Review Letters*, **2012**, 109, 187603	7.4	176
221	Divacancy in 4H-SiC. *Physical Review Letters*, **2006**, 96, 055501	7.4	151
220	Electrically active defects in n-type 4H-silicon carbide grown in a vertical hot-wall reactor. *Journal of Applied Physics*, **2003**, 93, 4708-4714	2.5	141
219	Negative-U centers in 4H silicon carbide. *Physical Review B*, **1998**, 58, R10119-R10122	3.3	127
218	Growth of SiC by "Hot-Wall" CVD and HTCVD. *Physica Status Solidi (B): Basic Research*, **1997**, 202, 321-334	1.3	115
217	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. *Nature Communications*, **2019**, 10, 1954	17.4	99
216	Ab initio density-functional supercell calculations of hydrogen defects in cubic SiC. *Physical Review B*, **2001**, 63,	3.3	99
215	Aggregation of carbon interstitials in silicon carbide: A theoretical study. *Physical Review B*, **2003**, 68,	3.3	94
214	Carbon vacancy-related defect in 4H and 6H SiC. *Physical Review B*, **2001**, 63,	3.3	93
213	Electron effective masses in 4H SiC. *Applied Physics Letters*, **1995**, 66, 1074-1076	3.4	89
212	Electrical and optical control of single spins integrated in scalable semiconductor devices. *Science*, **2019**, 366, 1225-1230	33.3	88
211	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. *Nano Letters*, **2017**, 17, 1782-1786	11.5	85
210	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. *Physical Review X*, **2017**, 7,	9.1	78

209	The silicon vacancy in SiC. *Physica B: Condensed Matter*, **2009**, 404, 4354-4358	2.8	70
208	Conjugated Polyelectrolyte Blends for Electrochromic and Electrochemical Transistor Devices. *Chemistry of Materials*, **2015**, 27, 6385-6393	9.6	67
207	Identification of the carbon antisite-vacancy pair in 4H-SiC. *Physical Review Letters*, **2006**, 96, 145501	7.4	66
206	Correlation between the antisite pair and the DI center in SiC. *Physical Review B*, **2003**, 67,	3.3	66
205	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. *Physical Review Applied*, **2018**, 9,	4.3	65
204	Electron effective masses and mobilities in high-purity 6H□SiC chemical vapor deposition layers. *Applied Physics Letters*, **1994**, 65, 3209-3211	3.4	65
203	Liquid phase epitaxial growth of SiC. *Journal of Crystal Growth*, **1999**, 197, 147-154	1.6	62
202	Photoexcitation-electron-paramagnetic-resonance studies of the carbon vacancy in 4H-SiC. *Applied Physics Letters*, **2002**, 81, 3945-3947	3.4	60
201	Determination of the electron effective-mass tensor in 4H SiC. *Physical Review B*, **1996**, 53, 15409-15412	3.3	60
200	EPR identification of intrinsic defects in SiC. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 1298-1314	1.3	56
199	Defects and carrier compensation in semi-insulating 4H□SiC substrates. *Physical Review B*, **2007**, 75,	3.3	56
198	EPR and theoretical studies of negatively charged carbon vacancy in 4H□SiC. *Physical Review B*, **2005**, 71,	3.3	53
197	Vector Magnetometry Using Silicon Vacancies in 4H-SiC Under Ambient Conditions. *Physical Review Applied*, **2016**, 6,	4.3	52
196	Identification of Si-vacancy related room-temperature qubits in 4H silicon carbide. *Physical Review B*, **2017**, 96,	3.3	51
195	Stark tuning and electrical charge state control of single divacancies in silicon carbide. *Applied Physics Letters*, **2017**, 111, 262403	3.4	51
194	Defects in High-Purity Semi-Insulating SiC. *Materials Science Forum*, **2004**, 457-460, 437-442	0.4	51
193	Capture cross sections of electron irradiation induced defects in 6H□SiC. *Journal of Applied Physics*, **1998**, 84, 704-708	2.5	49
192	HTCVD Grown Semi-Insulating SiC Substrates. *Materials Science Forum*, **2003**, 433-436, 33-38	0.4	47

191	Developing silicon carbide for quantum spintronics. *Applied Physics Letters*, **2020**, 116, 190501	3.4	45
190	High quality 4H-SiC epitaxial layers grown by chemical vapor deposition. *Applied Physics Letters*, **1995**, 66, 1373-1375	3.4	45
189	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. *Applied Physics Letters*, **2013**, 102, 112106	3.4	44
188	Electronic properties of the residual donor in unintentionally doped β-Ga2O3. *Journal of Applied Physics*, **2016**, 120, 235703	2.5	44
187	EPR and theoretical studies of positively charged carbon vacancy in 4H-SiC. *Physical Review B*, **2004**, 70,	3.3	43
186	Resonant optical spectroscopy and coherent control of Cr4+ spin ensembles in SiC and GaN. *Physical Review B*, **2017**, 95,	3.3	42
185	Stable and metastable Si negative-U centers in AlGaN and AlN. *Applied Physics Letters*, **2014**, 105, 162106	3.4	41
184	Shallow donor and DX states of Si in AlN. *Applied Physics Letters*, **2011**, 98, 092104	3.4	41
183	Identification of the gallium vacancy-oxygen pair defect in GaN. *Physical Review B*, **2009**, 80,	3.3	40
182	Entanglement and control of single nuclear spins in isotopically engineered silicon carbide. *Nature Materials*, **2020**, 19, 1319-1325	27	40
181	Negative-U carbon vacancy in 4H-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. *Physical Review B*, **2013**, 88,	3.3	39
180	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and 6H-SiC. *Physical Review B*, **2002**, 66,	3.3	39
179	Intrinsic Defects in Silicon Carbide Polytypes. *Materials Science Forum*, **2001**, 353-356, 499-504	0.4	37
178	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. *Nano Letters*, **2019**, 19, 7173-7180	11.5	36
177	Hole effective masses in 4H SiC. *Physical Review B*, **2000**, 61, R10544-R10546	3.3	36
176	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. *Npj Quantum Information*, **2018**, 4,	8.6	35
175	Overcoordinated hydrogens in the carbon vacancy: donor centers of SiC. *Physical Review Letters*, **2000**, 84, 4926-9	7.4	34
174	Silicon antisite in 4H SiC. *Physical Review Letters*, **2001**, 87, 045502	7.4	34

173	Electronic properties of Si-doped Alx Ga1−xN with aluminum mole fractions above 80%. *Journal of Applied Physics*, **2016**, 120, 145702	2.5	34
172	Quantitative comparison between Z1/2 center and carbon vacancy in 4H-SiC. *Journal of Applied Physics*, **2014**, 115, 143705	2.5	33
171	Group-II acceptors in wurtzite AlN: A screened hybrid density functional study. *Applied Physics Letters*, **2010**, 96, 192110	3.4	33
170	Optically detected magnetic resonance studies of defects in electron-irradiated 3C SiC layers. *Physical Review B*, **1997**, 55, 2863-2866	3.3	33
169	Water adsorption on fullerene-like carbon nitride overcoats. *Thin Solid Films*, **2008**, 517, 1106-1110	2.2	33
168	Excitation properties of the divacancy in 4H-SiC. *Physical Review B*, **2018**, 98,	3.3	33
167	Optical Properties of Vanadium in 4H Silicon Carbide for Quantum Technology. *Physical Review Applied*, **2019**, 12,	4.3	32
166	Electrical characterization of metastable carbon clusters in SiC: A theoretical study. *Physical Review B*, **2006**, 73,	3.3	32
165	Observation of negative-U centers in 6H silicon carbide. *Applied Physics Letters*, **1999**, 74, 839-841	3.4	32
164	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. *Journal of Applied Physics*, **1999**, 86, 4348-4353	2.5	31
163	Vibronic States and Their Effect on the Temperature and Strain Dependence of Silicon-Vacancy Qubits in 4H-SiC. *Physical Review Applied*, **2020**, 13,	4.3	29
162	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in 3C-, 4H-, and 6H-SiC. *Physical Review B*, **2006**, 73,	3.3	29
161	The complex impact of silicon and oxygen on the n-type conductivity of high-Al-content AlGaN. *Applied Physics Letters*, **2013**, 102, 132113	3.4	28
160	Defects in Semi-Insulating SiC Substrates. *Materials Science Forum*, **2003**, 433-436, 45-50	0.4	28
159	Carbon-vacancy related defects in 4H- and 6H-SiC. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 61-62, 202-206	3.1	28
158	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. *Semiconductor Science and Technology*, **1999**, 14, 1141-1146	1.8	28
157	Dominant recombination center in electron-irradiated 3C SiC. *Journal of Applied Physics*, **1996**, 79, 3784-3786	2.5	28
156	Stabilization of point-defect spin qubits by quantum wells. *Nature Communications*, **2019**, 10, 5607	17.4	28

155	Theory of Neutral Divacancy in SiC: A Defect for Spintronics. *Materials Science Forum*, **2010**, 645-648, 395-397	0.4	27
154	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. *Materials Science Forum*, **2000**, 338-342, 131-136	0.4	27
153	First principles predictions of magneto-optical data for semiconductor point defect identification: the case of divacancy defects in 4HSiC. *New Journal of Physics*, **2018**, 20, 023035	2.9	25
152	Impurity-controlled dopant activation: Hydrogen-determined site selection of boron in silicon carbide. *Applied Physics Letters*, **2001**, 79, 2746-2748	3.4	25
151	Possible lifetime-limiting defect in 6H SiC. *Applied Physics Letters*, **1994**, 65, 2687-2689	3.4	25
150	Spin-controlled generation of indistinguishable and distinguishable photons from silicon vacancy centres in silicon carbide. *Nature Communications*, **2020**, 11, 2516	17.4	24
149	Clustering of vacancy defects in high-purity semi-insulating SiC. *Physical Review B*, **2007**, 75,	3.3	24
148	SiC a semiconductor for high-power, high-temperature and high-frequency devices. *Physica Scripta*, **1994**, T54, 283-290	2.6	24
147	Coherent electrical readout of defect spins in silicon carbide by photo-ionization at ambient conditions. *Nature Communications*, **2019**, 10, 5569	17.4	24
146	Asymmetric split-vacancy defects in SiC polytypes: a combined theoretical and electron spin resonance study. *Physical Review Letters*, **2011**, 107, 195501	7.4	22
145	Ab initio supercell calculations on aluminum-related defects in SiC. *Physical Review B*, **2007**, 75,	3.3	22
144	Bright single photon sources in lateral silicon carbide light emitting diodes. *Applied Physics Letters*, **2018**, 112, 231103	3.4	21
143	Optically detected cyclotron resonance investigations on 4H and 6H SiC: Band-structure and transport properties. *Physical Review B*, **2000**, 61, 4844-4849	3.3	21
142	Effective Masses in SiC Determined by Cyclotron Resonance Experiments. *Physica Status Solidi A*, **1997**, 162, 79-93		20
141	Electron-paramagnetic-resonance identification of silver centers in silicon. *Physical Review B*, **1992**, 46, 4544-4550	3.3	20
140	Electron paramagnetic resonance and theoretical study of gallium vacancy in Ga2O3. *Applied Physics Letters*, **2020**, 117, 032101	3.4	19
139	Boron Centers in 4H-SiC. *Materials Science Forum*, **2001**, 353-356, 455-458	0.4	18
138	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. *Applied Physics Letters*, **2014**, 105, 102103	3.4	17

137	Recombination centers in as-grown and electron-irradiated ZnO substrates. *Journal of Applied Physics*, **2007**, 102, 093504	2.5	17
136	Diffusion of hydrogen in perfect, p-type doped, and radiation-damaged 4H□SiC. *Physical Review B*, **2004**, 69,	3.3	17
135	Defects in SiC. *Physica B: Condensed Matter*, **2003**, 340-342, 15-24	2.8	17
134	Silicon vacancy related TV2a center in 4H-SiC. *Physical Review B*, **2003**, 68,	3.3	17
133	Metastable defects in 6H□SiC: experiments and modeling. *Journal of Applied Physics*, **2002**, 91, 1324-1330	2.5	17
132	Paramagnetic state of the isolated gold impurity in silicon. *Physical Review Letters*, **1992**, 69, 3185-3188	7.4	17
131	Theoretical and electron paramagnetic resonance studies of hyperfine interaction in nitrogen doped 4H and 6H SiC. *Journal of Applied Physics*, **2014**, 115, 073705	2.5	16
130	Theoretical study of small silicon clusters in 4H□SiC. *Physical Review B*, **2007**, 76,	3.3	16
129	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. *Materials Science Forum*, **1998**, 264-268, 123-126	0.4	16
128	Identification of divacancy and silicon vacancy qubits in 6H-SiC. *Applied Physics Letters*, **2019**, 114, 112107	3.4	15
127	Prominent defects in semi-insulating SiC substrates. *Physica B: Condensed Matter*, **2007**, 401-402, 67-72	2.8	15
126	Hydrogen passivation of nitrogen in SiC. *Applied Physics Letters*, **2003**, 83, 1385-1387	3.4	15
125	Spectrally reconfigurable quantum emitters enabled by optimized fast modulation. *Npj Quantum Information*, **2020**, 6,	8.6	15
124	Intrinsic defects in high-purity SiC. *Microelectronic Engineering*, **2006**, 83, 130-134	2.5	14
123	Calculation of Hyperfine Constants of Defects in 4H-SiC. *Materials Science Forum*, **2003**, 433-436, 511-514	0.4	14
122	Electron paramagnetic resonance of nickel in silicon. □. Identification of spectrum. *Solid State Communications*, **1990**, 73, 393-398	1.6	14
121	Capacitance transient studies of electron irradiated 4H-SiC. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1997**, 46, 336-339	3.1	13
120	Activation of shallow boron acceptor in CB coimplanted silicon carbide: A theoretical study. *Applied Physics Letters*, **2005**, 86, 102108	3.4	13

119	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. *Physica B: Condensed Matter*, **2012**, 407, 1462-1466	2.8	12
118	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. *Journal of Physics Condensed Matter*, **2013**, 25, 335804	1.8	12
117	Pulsed EPR studies of Phosphorus shallow donors in diamond and SiC. *Physica B: Condensed Matter*, **2006**, 376-377, 358-361	2.8	12
116	Hyperfine interaction of the nitrogen donor in 4H SiC. *Physical Review B*, **2004**, 70,	3.3	12
115	Passivation of p-type dopants in 4H-SiC by hydrogen. *Physica B: Condensed Matter*, **2001**, 308-310, 722-725	2.8	12
114	Magnetic resonance spectroscopy in silver-doped silicon. *Journal of Applied Physics*, **1993**, 73, 1797-1801	2.5	12
113	Donor and double-donor transitions of the carbon vacancy related EH6/7 deep level in 4H-SiC. *Journal of Applied Physics*, **2016**, 119, 235703	2.5	12
112	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. *Applied Physics Letters*, **2019**, 114, 212105	3.4	11
111	Hole effective masses in 6H-SiC from optically detected cyclotron resonance. *Physical Review B*, **2002**, 66,	3.3	11
110	Fabrication and nanophotonic waveguide integration of silicon carbide colour centres with preserved spin-optical coherence. *Nature Materials*, **2021**,	27	11
109	EPR and ab initio calculation study on the EI4 center in 4H- and 6H-SiC. *Physical Review B*, **2010**, 82,	3.3	10
108	Electron paramagnetic resonance and theoretical studies of Nb in 4H- and 6H-SiC. *Journal of Applied Physics*, **2012**, 112, 083711	2.5	10
107	Identification of a Frenkel-pair defect in electron-irradiated 3C SiC. *Physical Review B*, **2009**, 80,	3.3	10
106	Optical and morphological features of bulk and homoepitaxial ZnO. *Superlattices and Microstructures*, **2006**, 39, 247-256	2.8	10
105	Divacancy and Its Identification: Theory. *Materials Science Forum*, **2006**, 527-529, 523-526	0.4	10
104	Deep levels and carrier compensation in V-doped semi-insulating 4H-SiC. *Applied Physics Letters*, **2007**, 91, 202111	3.4	10
103	Electronic structure of a photoluminescent center in silver-doped silicon. *Physical Review B*, **1994**, 49, 17428-17431	3.3	10
102	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. *Journal of Physics Condensed Matter*, **2019**, 31, 195501	1.8	9

101	Exciton luminescence in AlN triggered by hydrogen and thermal annealing. *Applied Physics Letters*, **2015**, 106, 242101	3.4	9
100	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure 28Si12C, Natural and 13C Enriched 4H-SiC. *Materials Science Forum*, **2014**, 778-780, 471-474	0.4	9
99	Deep levels in low-energy electron-irradiated 4H-SiC. *Physica Status Solidi - Rapid Research Letters*, **2009**, 3, 121-123	2.5	9
98	EPR and ENDOR Studies of Shallow Donors in SiC. *Applied Magnetic Resonance*, **2010**, 39, 49-85	0.8	9
97	Annealing Behaviour of Vacancy-and Antisite-Related Defects in Electron-Irradiated 4H-SiC. *Materials Science Forum*, **2004**, 457-460, 473-476	0.4	9
96	Possibility for the electrical activation of the carbon antisite by hydrogen in SiC. *Physical Review B*, **2005**, 71,	3.3	9
95	A Complex Defect Related to the Carbon Vacancy in 4H and 6H SiC. *Physica Scripta*, **1999**, T79, 46	2.6	9
94	Electron paramagnetic resonance of nickel in silicon II. hyperfine and quadrupole interactions. *Solid State Communications*, **1991**, 80, 439-445	1.6	9
93	Five-second coherence of a single spin with single-shot readout in silicon carbide.. *Science Advances*, **2022**, 8, eabm5912	14.3	9
92	On the behavior of silicon donor in conductive AlxGa1xN (0.63 x 1). *Physica Status Solidi (B): Basic Research*, **2015**, 252, 1306-1310	1.3	8
91	Negative-U behavior of the Si donor in Al0.77Ga0.23N. *Applied Physics Letters*, **2013**, 103, 042101	3.4	8
90	Defects at nitrogen site in electron-irradiated AlN. *Applied Physics Letters*, **2011**, 98, 242116	3.4	8
89	Deep luminescent centres in electron-irradiated 6H SiC. *Diamond and Related Materials*, **1997**, 6, 1378-1380	3.9	8
88	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. *Materials Science Forum*, **2002**, 389-393, 501-504	0.4	8
87	Theoretical Investigation of an Intrinsic Defect in SiC. *Materials Science Forum*, **2002**, 389-393, 477-480	0.4	8
86	The Neutral Silicon Vacancy in 6H and 4H SiC. *Materials Science Forum*, **1998**, 264-268, 473-476	0.4	8
85	Electron-paramagnetic-resonance studies of defects in electron-irradiated p-type 4H and 6H SiC. *Physica B: Condensed Matter*, **1999**, 273-274, 655-658	2.8	8
84	CVD-Growth of Low-Doped 6H SIC Epitaxial Films. *Materials Research Society Symposia Proceedings*, **1994**, 339, 405		8

83	The Electronic Structure of Platinum, Palladium and Nickel in Silicon. *Materials Science Forum*, **1991**, 38-41, 355-360	0.4	8
82	Silicon in AlN: shallow donor and DX behaviors. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2167-2169		7
81	Anti-site pair in SiC: a model of the DI center. *Physica B: Condensed Matter*, **2003**, 340-342, 175-179	2.8	7
80	Electronic Structure of Deep Defects in SiC. *Advanced Texts in Physics*, **2004**, 461-492		7
79	Vacancies and their Complexes with H in SiC. *Materials Science Forum*, **2000**, 338-342, 817-820	0.4	7
78	Spin-relaxation times exceeding seconds for color centers with strong spin–orbit coupling in SiC. *New Journal of Physics*, **2020**, 22, 103051	2.9	7
77	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. *Journal of Applied Physics*, **2016**, 119, 095707	2.5	7
76	The Silicon Vacancy in SiC. *Materials Science Forum*, **2009**, 615-617, 347-352	0.4	6
75	Divacancy Model for P6/P7 Centers in 4H- and 6H-SiC. *Materials Science Forum*, **2006**, 527-529, 527-530	0.4	6
74	Electron Paramagnetic Resonance Study of the HEI4/SI5 Center in 4H-SiC. *Materials Science Forum*, **2006**, 527-529, 543-546	0.4	6
73	The Carbon Vacancy Pair in 4H and 6H SiC. *Materials Science Forum*, **2000**, 338-342, 821-824	0.4	6
72	Optically Detected Magnetic Resonance Studies of Non-Radiative Recombination Centres in 6H SiC. *Materials Science Forum*, **1998**, 264-268, 599-602	0.4	6
71	Shallow excited states of deep luminescent centers in silicon. *Solid State Communications*, **1995**, 93, 415-418	1.8	6
70	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. *Physical Review B*, **2015**, 92,	3.3	5
69	Shallow donor in natural MoS2. *Physica Status Solidi - Rapid Research Letters*, **2015**, 9, 707-710	2.5	5
68	Characterization of the nitrogen split interstitial defect in wurtzite aluminum nitride using density functional theory. *Journal of Applied Physics*, **2014**, 116, 113702	2.5	5
67	Magnetic characterization of conductance electrons in GaN. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1728-1731	1.3	5
66	A Deep Photoluminescence Band in 4H SiC Related to the Silicon Vacancy. *Materials Science Forum*, **1997**, 258-263, 685-690	0.4	5

65	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. *Materials Science Forum*, **2005**, 483-485, 515-518	0.4	5
64	Theoretical Investigations of Complexes of p-Type Dopants and Carbon Interstitial in SiC: Bistable, Negative-U Defects. *Materials Science Forum*, **2005**, 483-485, 519-522	0.4	5
63	Observation of Metastable Defect in Electron Irradiated 6H-SiC. *Materials Science Forum*, **1998**, 264-268, 561-564	0.4	5
62	Configuration transformation of metastable defects in 6H-SiC. *Semiconductor Science and Technology*, **1999**, 14, 251-256	1.8	5
61	Ligand ENDOR on substitutional manganese in GaAs. *Physical Review B*, **1994**, 49, 10999-11004	3.3	5
60	n-Type conductivity bound by the growth temperature: the case of Al0.72Ga0.28N highly doped by silicon. *Journal of Materials Chemistry C*, **2016**, 4, 8291-8296	7.1	4
59	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study **2014**,		4
58	Radiation-induced defects in GaN. *Physica Scripta*, **2010**, T141, 014015	2.6	4
57	Effects of microwave fields on recombination processes in 4H and 6H SiC. *Journal of Applied Physics* , **1997**, 81, 1929-1932	2.5	4
56	Intrinsic Defects in HPSI 6H-SiC: an EPR Study. *Materials Science Forum*, **2008**, 600-603, 381-384	0.4	4
55	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. *Journal of Crystal Growth*, **2008**, 310, 1006-1009	1.6	4
54	Identification of divacancies in 4H-SiC. *Physica B: Condensed Matter*, **2006**, 376-377, 334-337	2.8	4
53	Chromium in 4H and 6H SiC: Photoluminescence and Zeeman Studies. *Materials Science Forum*, **1998**, 264-268, 603-606	0.4	4
52	Cyclotron Resonance Studies of Effective Masses and Band Structure in SiC. *Advanced Texts in Physics*, **2004**, 437-460		4
51	Charge state control of the silicon vacancy and divacancy in silicon carbide. *Journal of Applied Physics*, **2021**, 129, 215702	2.5	4
50	Towards identification of silicon vacancy-related electron paramagnetic resonance centers in 4H-SiC. *Physical Review B*, **2021**, 104,	3.3	4
49	Identification of Niobium in 4H-SiC by EPR and Ab Initio Studies. *Materials Science Forum*, **2012**, 717-720, 217-220	0.4	3
48	Signature of the Negative Carbon Vacancy-Antisite Complex. *Materials Science Forum*, **2006**, 527-529, 539-542	0.4	3

47	A Theoretical Study on Aluminium-Related Defects in SiC. *Materials Science Forum*, **2007**, 556-557, 445-448	0.4	3
46	Intrinsic Defects in Semi-Insulating SiC: Deep Levels and their Roles in Carrier Compensation. *Materials Science Forum*, **2007**, 556-557, 465-468	0.4	3
45	As-Grown and Process-Induced Intrinsic Deep-Level Luminescence in 4H-SiC. *Materials Science Forum*, **2001**, 353-356, 365-368	0.4	3
44	Impurity-Controlled Dopant Activation - The Role of Hydrogen in p-Type Doping of SiC. *Materials Science Forum*, **2002**, 389-393, 561-564	0.4	3
43	Narrow inhomogeneous distribution of spin-active emitters in silicon carbide. *Applied Physics Letters*, **2021**, 118, 144003	3.4	3
42	Electronic properties of defects in high-fluence electron-irradiated bulk GaN. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 521-526	1.3	3
41	Deep levels related to the carbon antisite□acancy pair in 4H-SiC. *Journal of Applied Physics*, **2021**, 130, 065703	2.5	3
40	Silicon and Oxygen in High-Al-Content AlGaN: Incorporation Kinetics and Electron Paramagnetic Resonance Study. *Solid State Phenomena*, **2013**, 205-206, 441-445	0.4	2
39	Defects Introduced by Electron-Irradiation at Low Temperatures in SiC. *Materials Science Forum*, **2009**, 615-617, 377-380	0.4	2
38	Transition Metal Defects in Cubic and Hexagonal Polytypes of SiC: Site Selection, Magnetic and Optical Properties from Ab Initio Calculations. *Materials Science Forum*, **2012**, 717-720, 205-210	0.4	2
37	Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers. *Diamond and Related Materials*, **1997**, 6, 1381-1384	3.5	2
36	EPR Identification of Defects and Impurities in SiC: To be Decisive. *Materials Science Forum*, **2008**, 600-603, 279-284	0.4	2
35	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. *Physica B: Condensed Matter*, **2007**, 401-402, 507-510	2.8	2
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